

MOSFET N-CH 100V 80A TO252-3

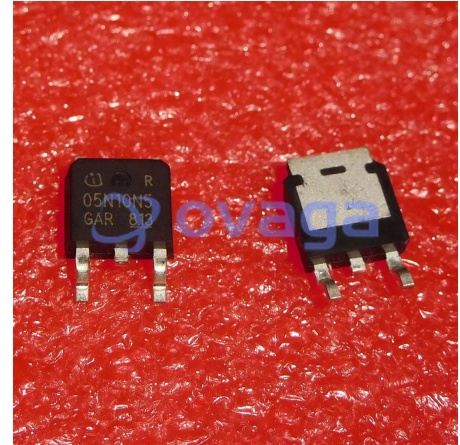
Manufacturers [Infineon Technologies Corporation](#)

Package/Case TO-252

Product Type Transistors

RoHS

Lifecycle



Images are for reference only

Please submit RFQ for IPD050N10N5 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPD050N10N5 is a specific model number for a power MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor) that is manufactured by Infineon Technologies AG, a semiconductor company headquartered in Germany.

Features

It has a drain-source voltage (VDS) rating of 100V.

It can handle a continuous drain current (ID) of 50A.

It has a low on-resistance (RDS(on)) of 5 mOhm, which means it can conduct current with low power loss.

It is designed to operate at high switching frequencies, which makes it suitable for various power electronics applications.

Application

DC-DC converters and switching regulators

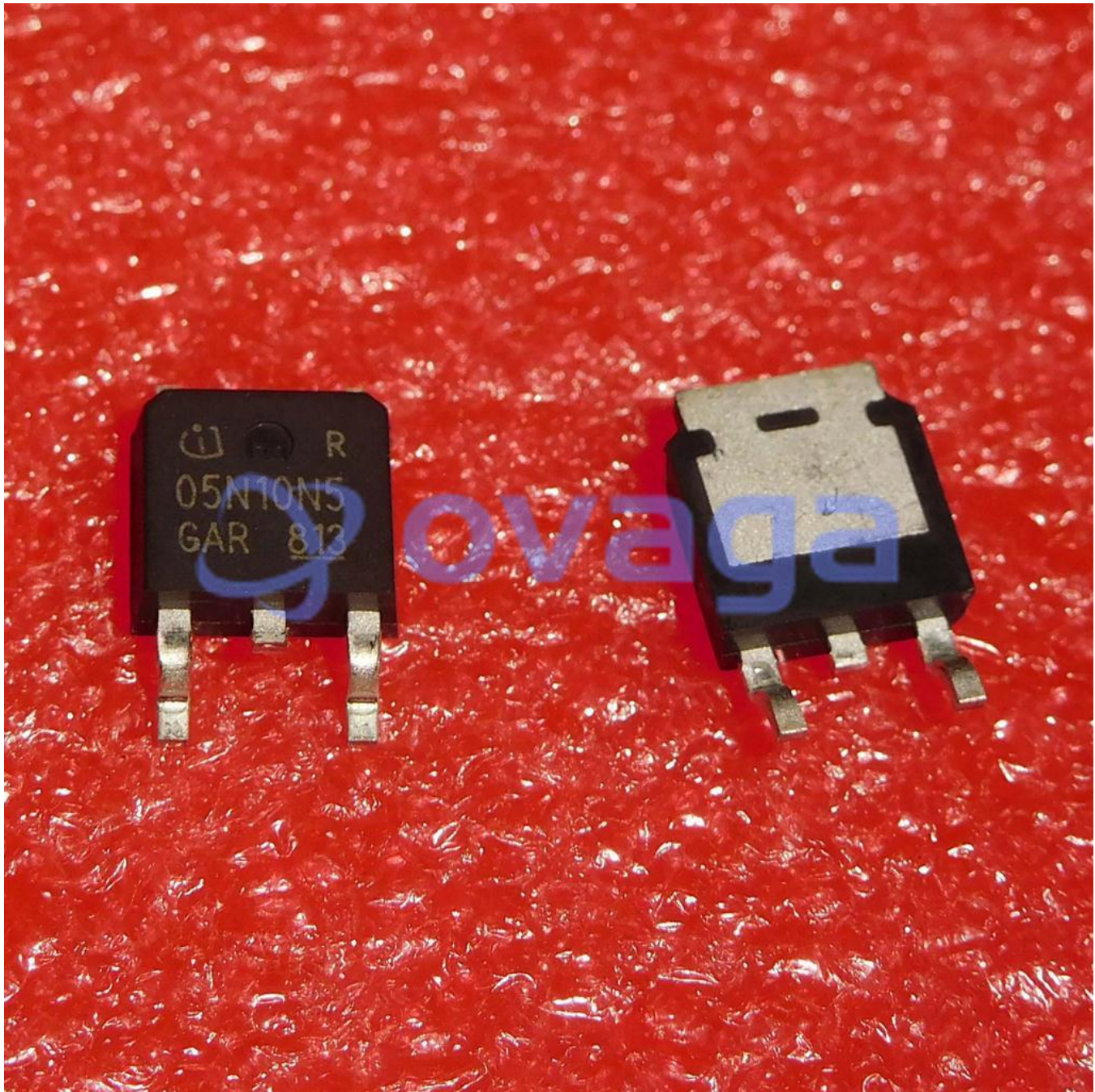
Motor control

Solar power inverters

Uninterruptible power supplies (UPS)

Battery management systems

Electric vehicle (EV) charging stations



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



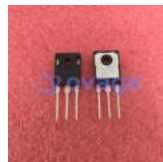
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

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[IPD180N10N3G](#)

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